

L Number	Hits	Search Text	DB	Time stamp
1	990	(349/5).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/06 07:57
2	18	((scan scanning) near line with (gate electrode) and ((349/5).CCLS.))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/06 07:57
3	15	((channel with (si silicon poly polysilicon semiconduct\$4)) and ((349/5).CCLS.))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/06 07:57
4	159	(349/46).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/06 07:57
5	36	((scan scanning) near line with (gate electrode) and ((349/46).CCLS.))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/06 07:57
6	102	((channel with (si silicon poly polysilicon semiconduct\$4)) and ((349/46).CCLS.)) (((scan scanning) near line with (gate electrode) and ((349/46).CCLS.)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/06 07:57

L Number	Hits	Search Text	DB	Time stamp
3	20	((scan scanning) near line with (gate electrode) and (257/72).CCLS.) and @pd>=20040130 ((scan scanning) near line with (gate electrode) and (257/222,225).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/04 15:48